

Rafal Jakiela

List of Publications by Year in descending order

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208
papers

2,847
citations

236612

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42
g-index

211
all docs

211
docs citations

211
times ranked

3130
citing authors

#	ARTICLE	IF	CITATIONS
1	Effects of electron concentration on the optical absorption edge of InN. Applied Physics Letters, 2004, 84, 2805-2807.	1.5	221
2	ALD grown zinc oxide with controllable electrical properties. Semiconductor Science and Technology, 2012, 27, 074011.	1.0	134
3	Paramagnetic GaN:Fe and ferromagnetic (Ga,Fe)N: The relationship between structural, electronic, and magnetic properties. Physical Review B, 2007, 75, .	1.1	109
4	Structural and paramagnetic properties of dilute $Ga_{1-x}Mn_xN$. Physical Review B, 2010, 81, .	1.1	70
5	Experimental probing of exchange interactions between localized spins in the dilute magnetic insulator (Ga,Mn)N. Physical Review B, 2011, 84, .	1.1	61
6	Phase diagram and critical behavior of the random ferromagnet $Ga_{1-x}Mn_xN$. Physical Review B, 2013, 88, .	1.1	53
7	Photoluminescence study and structural characterization of p-type ZnO doped by N and/or As acceptors. Semiconductor Science and Technology, 2007, 22, 10-14.	1.0	49
8	$Ga_{1-x}Mn_xN$ epitaxial films with high magnetization. Applied Physics Letters, 2012, 101, .	1.5	48
9	Transparent p-type ZnO films obtained by oxidation of sputter-deposited Zn ₃ N ₂ . Solid State Communications, 2005, 135, 11-15.	0.9	47
10	Manipulating Mn ²⁺ /Mg ²⁺ cation complexes to control the charge- and spin-state of Mn in GaN. Scientific Reports, 2012, 2, 722.	1.6	43
11	Homogeneous and heterogeneous magnetism in (Zn,Co)O: From a random antiferromagnet to a dipolar superferromagnet by changing the growth temperature. Physical Review B, 2013, 88, .	1.1	43
12	Magnetic properties of ZnMnO films grown at low temperature by atomic layer deposition. Applied Physics Letters, 2006, 89, 051907.	1.5	38
13	The uniformity of Al distribution in aluminum-doped zinc oxide films grown by atomic layer deposition. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2011, 176, 237-241.	1.7	38
14	Vertically stacked non-volatile memory devices – material considerations. Microelectronic Engineering, 2008, 85, 2434-2438.	1.1	37
15	p-type conducting ZnO: fabrication and characterisation. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 1119-1124.	0.8	36
16	High Pressure Processing of Ion Implanted GaN. Electronics (Switzerland), 2020, 9, 1380.	1.8	36
17	The chemical vapour transport growth of ZnO single crystals. Journal of Alloys and Compounds, 2004, 371, 150-152.	2.8	34
18	Low temperature growth of ZnMnO: A way to avoid inclusions of foreign phases and spinodal decomposition. Applied Physics Letters, 2007, 90, 082502.	1.5	33

#	ARTICLE	IF	CITATIONS
19	Stretching magnetism with an electric field in a nitride semiconductor. Nature Communications, 2016, 7, 13232.	5.8	33
20	Substrate misorientation induced strong increase in the hole concentration in Mg doped GaN grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2008, 93, 172117.	1.5	31
21	Interplay between localization and magnetism in (Ga,Mn)As and (In,Mn)As. Physical Review Materials, 2017, 1, .	0.9	28
22	Influence of growth conditions on the lattice constant and composition of (Ga,Mn)As. Applied Physics Letters, 2003, 82, 4678-4680.	1.5	27
23	Origin of Magnetic Circular Dichroism in GaMnAs: Giant Zeeman Splitting versus Spin Dependent Density of States. Physical Review Letters, 2009, 102, 247202.	2.9	27
24	Nitrogen doped <i>i</i> -type ZnO films and <i>p</i> - <i>n</i> homojunction. Semiconductor Science and Technology, 2015, 30, 015001.	1.0	27
25	Observation of surface states on heavily indium-doped SnTe(111), a superconducting topological crystalline insulator. Physical Review B, 2016, 93, .	1.1	27
26	X-ray photoelectron spectroscopy study of highly-doped ZnO:Al,N films grown at O-rich conditions. Journal of Alloys and Compounds, 2017, 722, 683-689.	2.8	27
27	Control of Mg doping of GaN in RF-plasma molecular beam epitaxy. Journal of Crystal Growth, 2005, 278, 443-448.	0.7	26
28	Hafnium dioxide as a passivating layer and diffusive barrier in ZnO/Ag Schottky junctions obtained by atomic layer deposition. Applied Physics Letters, 2011, 98, .	1.5	26
29	Plasma-assisted MBE growth of GaN on Si(111) substrates. Crystal Research and Technology, 2012, 47, 307-312.	0.6	26
30	Diffusion and impurity segregation in hydrogen-implanted silicon carbide. Journal of Applied Physics, 2014, 115, .	1.1	26
31	XPS study of arsenic doped ZnO grown by Atomic Layer Deposition. Journal of Alloys and Compounds, 2014, 582, 594-597.	2.8	25
32	Si diffusion in epitaxial GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1416-1419.	0.8	24
33	Common origin of ferromagnetism and band edge Zeeman splitting in GaMnAs at low Mn concentrations. Applied Physics Letters, 2007, 91, 171118.	1.5	24
34	The influence of the growth temperature and interruption time on the crystal quality of InGaAs/GaAs QW structures grown by MBE and MOCVD methods. Journal of Crystal Growth, 2008, 310, 2785-2792.	0.7	24
35	Hydrogen diffusion in GaN:Mg and GaN:Si. Journal of Alloys and Compounds, 2018, 747, 354-358.	2.8	24
36	Band structure evolution and the origin of magnetism in (Ga,Mn)As: From paramagnetic through superparamagnetic to ferromagnetic phase. Physical Review B, 2018, 97, .	1.1	24

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37	Fermi level and bands offsets determination in insulating (Ga,Mn)N/GaN structures. Scientific Reports, 2017, 7, 41877.	1.6	23
38	Optical observation of the recharging processes of manganese ions in YAlO ₃ :Mn crystals under radiation and thermal treatment. Journal of Physics Condensed Matter, 2006, 18, 5389-5403.	0.7	22
39	ZnO, ZnMnO and ZnCoO films grown by atomic layer deposition. Semiconductor Science and Technology, 2012, 27, 074009.	1.0	22
40	Electrical and mechanical stability of aluminum-doped ZnO films grown on flexible substrates by atomic layer deposition. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2014, 186, 15-20.	1.7	22
41	Influence of oxygen-rich and zinc-rich conditions on donor and acceptor states and conductivity mechanism of ZnO films grown by ALD—Experimental studies. Journal of Applied Physics, 2020, 127, .	1.1	22
42	Correlation between electrical conductivity and luminescence properties in $\hat{\Gamma}^2$ -Ga ₂ O ₃ :Cr ³⁺ and $\hat{\Gamma}^2$ -Ga ₂ O ₃ :Cr,Mg single crystals. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	0.9	22
43	Fe-Mg interplay and the effect of deposition mode in (Ga,Fe)N doped with Mg. Physical Review B, 2011, 84, .	1.1	21
44	Optical and electrical studies of arsenic—implanted HgCdTe films grown with molecular beam epitaxy on GaAs and Si substrates. Infrared Physics and Technology, 2017, 81, 52-58.	1.3	21
45	Dominant shallow donors in zinc oxide layers obtained by low-temperature atomic layer deposition: Electrical and optical investigations. Acta Materialia, 2014, 65, 69-75.	3.8	20
46	On the Formation of Ni-Based Ohmic Contacts to n-Type 4H-SiC. Materials Science Forum, 2009, 615-617, 573-576.	0.3	19
47	Characteristics of ZnO—As/GaN heterojunction diodes obtained by PA-MBE. Journal Physics D: Applied Physics, 2013, 46, 035101.	1.3	19
48	Diversity of contributions leading to the nominally n—type behavior of ZnO films obtained by low temperature Atomic Layer Deposition. Journal of Alloys and Compounds, 2017, 727, 902-911.	2.8	19
49	Structural Properties of Thin ZnO Films Deposited by ALD under O-Rich and Zn-Rich Growth Conditions and Their Relationship with Electrical Parameters. Materials, 2021, 14, 4048.	1.3	19
50	On the effect of periodic Mg distribution in GaN:—Mg. Applied Physics Letters, 2007, 90, 142108.	1.5	18
51	Impact of substrate temperature on magnetic properties of plasma-assisted molecular beam epitaxy grown (Ga,Mn)N. Journal of Alloys and Compounds, 2018, 747, 946-959.	2.8	18
52	Nitride-based quantum structures and devices on modified GaN substrates. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 1130-1134.	0.8	17
53	Seeded growth of bulk ZnO by chemical vapor transport. Physica Status Solidi (B): Basic Research, 2010, 247, 1457-1459.	0.7	17
54	Dual-acceptor doped $\langle i \rangle p \langle /i \rangle$ -ZnO:(As,Sb)/ $\langle i \rangle n \langle /i \rangle$ -GaN heterojunctions grown by PA-MBE as a spectrum selective ultraviolet photodetector. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 2072-2077.	0.8	17

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55	Ti-Al-N MAX Phase a Candidate for Ohmic Contacts to n-GaN. Acta Physica Polonica A, 2008, 114, 1061-1066.	0.2	16
56	Modification of the local atomic structure around Mn atoms in (Ga, Mn)As layers by high temperature annealing. Journal of Physics Condensed Matter, 2007, 19, 496205.	0.7	15
57	Effects related to deposition temperature of ZnCoO films grown by atomic layer deposition - uniformity of Co distribution, structural, optical, electrical and magnetic properties. Physica Status Solidi (B): Basic Research, 2010, 247, 1666-1670.	0.7	14
58	Contact superconductivity in In δ -PbTe junctions. Journal of Applied Physics, 2010, 108, 053714.	1.1	14
59	Secondary ions mass spectroscopy measurements of dopant impurities in highly stressed InGaN laser diodes. Applied Physics Letters, 2011, 98, .	1.5	14
60	Electrical parameters of ZnO films and ZnO-based junctions obtained by atomic layer deposition. Semiconductor Science and Technology, 2011, 26, 085013.	1.0	14
61	Electron beam induced current profiling of the p-ZnO:N<i>n</i>-GaN heterojunction. Applied Physics Letters, 2015, 106, .	1.5	14
62	Effects of MOVPE Growth Conditions on GaN Layers Doped with Germanium. Materials, 2021, 14, 354.	1.3	14
63	Coexistence of ferromagnetism and quantum Hall effect in Mn modulation-doped two-dimensional hole systems. Journal of Crystal Growth, 2009, 311, 2160-2162.	0.7	13
64	Magnetic, optical and electrical characterization of SiC doped with scandium during the PVT growth. Journal of Crystal Growth, 2015, 413, 86-93.	0.7	13
65	Structural and Electrical Parameters of ZnO Thin Films Grown by ALD with either Water or Ozone as Oxygen Precursors. Crystals, 2019, 9, 554.	1.0	13
66	Diffusion of Mn in gallium nitride: Experiment and modelling. Journal of Alloys and Compounds, 2019, 771, 215-220.	2.8	13
67	Puzzling magneto-optical properties of ZnMnO films. Optical Materials, 2010, 32, 680-684.	1.7	12
68	Role of interface in ferromagnetism of (Zn,Co)O films. Physica Status Solidi (B): Basic Research, 2011, 248, 1596-1600.	0.7	12
69	Contacts for High-Resistivity (Cd,Mn)Te Crystals. IEEE Transactions on Nuclear Science, 2011, 58, 347-353.	1.2	12
70	Atomic layer deposition of Zn $_{1-x}$ Mg $_x$ O:Al transparent conducting films. Journal of Materials Science, 2014, 49, 1512-1518.	1.7	12
71	Spatial distribution of optical coloration in single crystalline LiNbO $_3$ after high-temperature H $_2$ /air treatments. Optical Materials, 2017, 70, 106-115.	1.7	12
72	Structure-property relationships in ZnO:Al-hydroquinone films grown on flexible substrates by atomic and molecular layer deposition. Materials and Design, 2017, 119, 297-302.	3.3	12

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73	Cation diffusion in MBE-grown CdTe layers. <i>Thin Solid Films</i> , 2000, 367, 220-222.	0.8	11
74	Out- and in-diffusion of oxygen ¹⁶ O in silicon. <i>Semiconductor Science and Technology</i> , 2004, 19, 1311-1314.	1.0	11
75	Preparation and characterization of hexagonal MnTe and ZnO layers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005, 2, 1218-1223.	0.8	11
76	New Chemical Method of Obtaining Thick Ga _{1-x} Mn _x N Layers: A Prospective Spintronic Material. <i>Chemistry of Materials</i> , 2007, 19, 3139-3143.	3.2	11
77	Semi-insulating (Cd,Mn)Te:V crystals: Electrical contacts. <i>Physica Status Solidi (B): Basic Research</i> , 2007, 244, 1706-1713.	0.7	11
78	Oxygen diffusion into GaN from oxygen implanted GaN or Al ₂ O ₃ . <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 1513-1515.	0.8	11
79	Arsenic chemical state in MBE grown epitaxial ZnO layers "doped" with As, N and Sb. <i>Journal of Alloys and Compounds</i> , 2016, 687, 937-942.	2.8	11
80	Comprehensive investigation of the interfacial misfit array formation in GaSb/GaAs material system. <i>Applied Physics A: Materials Science and Processing</i> , 2018, 124, 1.	1.1	11
81	p-type ZnO and ZnMnO by oxidation of Zn(Mn)Te films. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 988-991.	0.8	10
82	Composite titanium nitride layers produced on the AZ91D magnesium alloy by a hybrid method including hydrothermal modification of the layer. <i>Applied Surface Science</i> , 2015, 346, 394-405.	3.1	10
83	Deep levels in the MBE ZnO:As/n-GaN diodes " Photoluminescence, electrical properties and deep level transient spectroscopy. <i>Journal of Alloys and Compounds</i> , 2018, 742, 296-303.	2.8	10
84	Ultrahigh sensitivity SIMS analysis of oxygen in silicon. <i>Surface and Interface Analysis</i> , 2018, 50, 729-733.	0.8	10
85	Role of intrinsic and extrinsic defects in H implanted hydrothermally grown ZnO. <i>Journal of Applied Physics</i> , 2019, 126, 125707.	1.1	10
86	GaAs _{1-x} Bi _x growth on Ge: anti-phase domains, ordering, and exciton localization. <i>Scientific Reports</i> , 2020, 10, 2002.	1.6	10
87	CdTe-based crystals with Mg, Se, or Mn as materials for X and gamma ray detectors: Selected physical properties. <i>Progress in Crystal Growth and Characterization of Materials</i> , 2021, 67, 100543.	1.8	10
88	Magnetic Properties of Epitaxial (Ge,Mn)Te Thin Films with Varying Crystal Stoichiometry. <i>Acta Physica Polonica A</i> , 2008, 114, 1159-1165.	0.2	10
89	Doping of low-temperature GaAs and GaMnAs with carbon. <i>Applied Physics Letters</i> , 2004, 85, 4678-4680.	1.5	9
90	Growth and structural properties of thick GaN layers obtained by sublimation sandwich method. <i>Journal of Crystal Growth</i> , 2007, 303, 395-399.	0.7	9

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91	Diluted magnetic semiconductors based on II ^{VI} , III ^{VI} , and IV ^{VI} compounds. <i>Low Temperature Physics</i> , 2009, 35, 62-70.	0.2	9
92	N and Al co-doping as a way to p-type ZnO without post-growth annealing. <i>Materials Research Express</i> , 2016, 3, 125907.	0.8	9
93	The chemical states of As 3d in highly doped ZnO grown by Molecular Beam Epitaxy and annealed in different atmospheres. <i>Thin Solid Films</i> , 2016, 605, 283-288.	0.8	9
94	Experimental and theoretical analysis of influence of barrier composition on optical properties of GaN/AlGaIn multi-quantum wells: Temperature- and pressure-dependent photoluminescence studies. <i>Journal of Alloys and Compounds</i> , 2018, 769, 1064-1071.	2.8	9
95	ZnO:Sb MBE layers with different Sb content-optical, electronic and structural analysis. <i>Journal of Alloys and Compounds</i> , 2019, 797, 1163-1172.	2.8	9
96	Conductance spectra of (Nb, Pb, In)/NbP superconductor/Weyl semimetal junctions. <i>Physical Review B</i> , 2020, 101, .	1.1	9
97	Nematicity of correlated systems driven by anisotropic chemical phase separation. <i>Physical Review Materials</i> , 2018, 2, .	0.9	9
98	Ferromagnetic Transition in Ge _{1-x} Mn _x Te Layers. <i>Acta Physica Polonica A</i> , 2009, 116, 904-906.	0.2	9
99	Diffusion and activation of Si implanted into GaAs. <i>Vacuum</i> , 2003, 70, 97-101.	1.6	8
100	Determination of Mn Acceptor Compensation in MBE-Grown GaMnAs via Magnetic Circular Dichroism (MCD). <i>IEEE Transactions on Magnetics</i> , 2007, 43, 3031-3033.	1.2	8
101	The ratio of interstitial to substitutional site occupation by Mn atoms in GaAs estimated by EXAFS. <i>Radiation Physics and Chemistry</i> , 2009, 78, S80-S85.	1.4	8
102	Effect of processing on microstructure of Si:Mn. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2009, 159-160, 99-102.	1.7	8
103	Relation between exciton splitting, magnetic circular dichroism, and magnetization in wurtzite Ga _{1-x} Mn _x Fe _{1-x} N. <i>Physical Review B</i> , 2013, 88, .	1.1	8
104	Photo-etching of HVPE-grown GaN: Revealing extended non-homogeneities induced by periodic carrier gas exchange. <i>Journal of Crystal Growth</i> , 2014, 403, 77-82.	0.7	8
105	Investigation of Cd _{1-x} Mg _x Te as possible materials for X and gamma ray detectors. <i>Journal of Crystal Growth</i> , 2018, 491, 73-76.	0.7	8
106	Evidence for the homogeneous ferromagnetic phase in (Ga,Mn)(Bi,As) epitaxial layers from muon spin relaxation spectroscopy. <i>Scientific Reports</i> , 2019, 9, 3394.	1.6	8
107	Investigation of diffusion mechanism of beryllium in GaN. <i>Physica B: Condensed Matter</i> , 2020, 594, 412316.	1.3	8
108	Improved-sensitivity integral SQUID magnetometry of (Ga,Mn)N thin films in proximity to Mg-doped GaN. <i>Journal of Alloys and Compounds</i> , 2021, 868, 159119.	2.8	8

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109	Defect Structure of High-Temperature-Grown GaMnSb/GaSb. Acta Physica Polonica A, 2010, 117, 341-343.	0.2	8
110	Schottky Junctions Based on the ALD-ZnO Thin Films for Electronic Applications. Acta Physica Polonica A, 2011, 120, A-17-A-21.	0.2	8
111	Thermally stable Ru-Si-O gate electrode for AlGaIn/GaN HEMT. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 1060-1064.	0.8	7
112	SEM, EDS and CL Investigations of ZnMnO and ZnCoO Layers Grown at Low Temperature by Atomic Layer Deposition. Microscopy and Microanalysis, 2010, 16, 810-811.	0.2	7
113	(Cd,Mn)Te detectors for characterization of X-ray emissions generated during laser-driven fusion experiments. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2010, 624, 649-655.	0.7	7
114	Growth and Characterization of (Cd, Mn)Te. IEEE Transactions on Nuclear Science, 2013, 60, 3805-3814.	1.2	7
115	Proton implantation for the isolation of AlGaAs/GaAs quantum cascade lasers. Semiconductor Science and Technology, 2016, 31, 075010.	1.0	7
116	Compositional, structural, and optical properties of atomic layer deposited tantalum oxide for optical fiber sensor overlays. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, .	0.9	7
117	Do We Understand Magnetic Properties of ZnMnO?. Acta Physica Polonica A, 2007, 112, 261-267.	0.2	7
118	Properties of ZnN films as substrate masks in liquid phase epitaxial lateral overgrowth of compound semiconductors. Crystal Research and Technology, 2005, 40, 492-497.	0.6	6
119	Diffusion of Mn in gallium arsenide. Journal of Alloys and Compounds, 2006, 423, 132-135.	2.8	6
120	Magneto spectroscopy of symmetric and anti-symmetric states in double quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 894-906.	1.3	6
121	Amorphous contact layers on (Cd,Mn)Te crystals. Journal of Crystal Growth, 2011, 320, 1-5.	0.7	6
122	Processing of AlGaAs/GaAs quantum-cascade structures for terahertz laser. Journal of Nanophotonics, 2015, 9, 093079.	0.4	6
123	Semiconductor crystals based on CdTe with Se " Some structural and optical properties. Journal of Crystal Growth, 2018, 498, 405-410.	0.7	6
124	ZnCoO Films Obtained at Low Temperature by Atomic Layer Deposition Using Organic Zinc and Cobalt Precursors. Acta Physica Polonica A, 2008, 114, 1235-1240.	0.2	6
125	XANES Studies of Mn K and L _{2,3} Edges in the (Ga, Mn)As Layers Modified by High Temperature Annealing. Acta Physica Polonica A, 2008, 114, 357-366.	0.2	6
126	ZnCoO Films by Atomic Layer Deposition - Influence of a Growth Temperature in Uniformity of Cobalt Distribution. Acta Physica Polonica A, 2009, 116, 921-923.	0.2	6

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127	The Role of Atmospheric Elements in the Wide Band-Gap Semiconductors. Acta Physica Polonica A, 2019, 136, 916-939.	0.2	6
128	Magneto-transport in single InGaAs quantum wells of different shapes. Crystal Research and Technology, 2003, 38, 407-415.	0.6	5
129	Diffusion and activation of Zn implanted into InP:S. Vacuum, 2005, 78, 417-422.	1.6	5
130	Periodic Mg distribution in GaN:Î-Mg and the effect of annealing on structural and optical properties. Applied Surface Science, 2008, 255, 731-733.	3.1	5
131	Arsenic incorporation in MBE-grown HgCdTe studied with the use of ion milling. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1618-1620.	0.8	5
132	Method of determination of AlGaAsSb layer composition in molecular beam epitaxy processes with regard to unintentional As incorporation. Journal of Applied Physics, 2011, 110, .	1.1	5
133	Effect of Nitrogen Doping on the Growth of 4H Polytype on the 6H-SiC Seed by PVT Method. Materials Science Forum, 2012, 717-720, 29-32.	0.3	5
134	Electrical and optical properties of CdHgTe films grown by molecular-beam epitaxy on silicon substrates. Semiconductors, 2012, 46, 1341-1345.	0.2	5
135	Growth of SiC by PVT method in the presence of cerium dopant. Journal of Crystal Growth, 2013, 377, 88-95.	0.7	5
136	Thermal stability of multilayer Ti ₂ AlN-based ohmic contacts to n-GaN in ambient air. Solid-State Electronics, 2014, 94, 15-19.	0.8	5
137	Growth of SiC by PVT method with different sources for doping by a cerium impurity, CeO ₂ or CeSi ₂ . Journal of Crystal Growth, 2014, 401, 677-680.	0.7	5
138	Infrared Reflectance Analysis of Epitaxial n-Type Doped GaN Layers Grown on Sapphire. Nanoscale Research Letters, 2017, 12, 397.	3.1	5
139	Electronic phase separation in insulating (Ga, Mn) As with low compensation: super-paramagnetism and hopping conduction. Journal of Physics Condensed Matter, 2018, 30, 095801.	0.7	5
140	Comparison of defect structure in Si and Ge ion implanted GaN epilayers by RBS/channeling. Nuclear Instruments & Methods in Physics Research B, 2019, 444, 74-79.	0.6	5
141	Analysis of defect structure in GaN epilayers doped with implanted Si ⁺ by RBS/c method. Nuclear Instruments & Methods in Physics Research B, 2019, 450, 248-251.	0.6	5
142	Nano-size defect layers in arsenic-implanted and annealed HgCdTe epitaxial films studied with transmission electron microscopy. Applied Nanoscience (Switzerland), 2020, 10, 4971-4976.	1.6	5
143	Hydrogen in As-grown and Annealed ZnO Films Grown by Atomic Layer Deposition. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2000318.	0.8	5
144	MOVPE strain layers " growth and application. Journal of Crystal Growth, 2000, 221, 20-25.	0.7	4

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145	Charge carrier parameters in the conductive channels of HEMTs. <i>Physica Status Solidi A</i> , 2003, 195, 127-132.	1.7	4
146	Parallel magnetotransport in multiple quantum well structures. <i>Low Temperature Physics</i> , 2004, 30, 858-866.	0.2	4
147	Influence of annealing on the properties of (Cd,Mn)Te crystals. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014, 11, 1528-1532.	0.8	4
148	Electrical and structural characterization of nitrogen doped ZnO layers grown at low temperature by atomic layer deposition. <i>Semiconductor Science and Technology</i> , 2014, 29, 085006.	1.0	4
149	Incorporation of oxygen in SiC implanted with hydrogen. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2015, 365, 146-149.	0.6	4
150	Tuning the properties of ALD-ZnO-based rectifying structures by thin dielectric film insertion – Modeling and experimental studies. <i>Journal of Alloys and Compounds</i> , 2017, 693, 1164-1173.	2.8	4
151	Influence of As doping on the properties of nonpolar ZnO. <i>Thin Solid Films</i> , 2021, 720, 138520.	0.8	4
152	Improving the Properties of Composite Titanium Nitride Layers on the AZ91D Magnesium Alloy Using Hydrothermal Treatment. <i>Materials</i> , 2021, 14, 5903.	1.3	4
153	Effect of rapid thermal annealing on short period {CdO/ZnO} _m SLs grown on m-Al ₂ O ₃ . <i>Materials Science in Semiconductor Processing</i> , 2022, 142, 106493.	1.9	4
154	ZnO and ZnO:Mn crystals obtained with the chemical vapour transport method. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004, 1, 884-887.	0.8	3
155	Characterization of 6H-SiC Single Crystals Grown by PVT Method Using Different Source Materials and Open or Closed Seed Backside. <i>Materials Science Forum</i> , 2009, 615-617, 19-22.	0.3	3
156	Structural properties and metallic conductivity of Ti _{1-x} Nb _x O ₂ films grown by atomic layer deposition on crystalline substrates. <i>Journal Physics D: Applied Physics</i> , 2015, 48, 495305.	1.3	3
157	The importance of structural inhomogeneity in GaN thin films. <i>Journal of Crystal Growth</i> , 2016, 456, 160-167.	0.7	3
158	SIMS accurate determination of matrix composition of topological crystalline insulator material Pb _{1-x} Sn _x Se. <i>Surface and Interface Analysis</i> , 2020, 52, 71-75.	0.8	3
159	Detection of Si doping in the AlN/GaN MQW using Super X EDS measurements. <i>Micron</i> , 2020, 134, 102864.	1.1	3
160	Schottky contacts to ZnO layers grown by Atomic Layer Deposition: effects of H ₂ O ₂ functionalization and transport mechanisms. <i>Applied Surface Science</i> , 2021, 552, 149067.	3.1	3
161	Ferromagnetism of Narrow-Gap Ge _{1-x} Y _x Mn _y Te and Layered In _{1-x} Mn _x Se Semiconductors. <i>Acta Physica Polonica A</i> , 2008, 114, 1219-1227.	0.2	3
162	ZnO Thin Films Deposited on Sapphire by High Vacuum High Temperature Sputtering. <i>Acta Physica Polonica A</i> , 2011, 119, 686-688.	0.2	3

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163	Investigation of beryllium diffusion in HVPE-GaN grown in [11 $\bar{2}$ 0] and [10-10] crystallographic directions. <i>Materials Science in Semiconductor Processing</i> , 2022, 139, 106332.	1.9	3
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